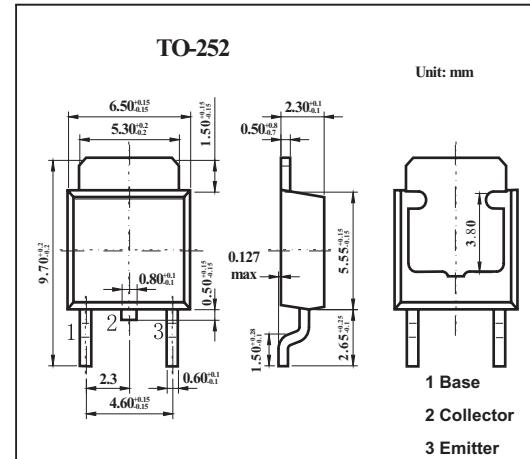


Silicon PNP Epitaxial Planar Type**2SB929****■ Features**

- High forward current transfer ratio hFE which has satisfactory linearity.
- Low collector-emitter saturation voltage VCE(sat).

■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CBO}	-60	V
Collector-emitter voltage	V _{CEO}	-60	V
Emitter-base voltage	V _{EBO}	-5	V
Collector current	I _C	-3	A
Peak collector current	I _{CP}	-5	A
Collector power dissipation	P _C	1.3	W
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector cutoff current	I _{CES}	V _{CE} = -60 V, V _{BE} = 0			-200	μA
	I _{CEO}	V _{CE} = -30 V, I _B = 0			-300	μA
Emitter-base cutoff current	I _{EBO}	V _{EB} = -5 V, I _C = 0			-1	mA
Collector-emitter voltage	V _{CEO}	I _C = -30 mA, I _B = 0	-60			V
Forward current transfer ratio	h _{FE}	V _{CE} = -4 V, I _C = -1 A	70	250		
		V _{CE} = -4 V, I _C = -3 A	10			
Base to emitter voltage	V _{BE}	V _{CE} = -4 V, I _C = -3 A			-1.8	V
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = -3 A, I _B = -0.375 A			-1.2	V
Transition frequency	f _T	V _{CE} = -10 V, I _C = -0.5 A, f = 10 MHz	30			MHz
Turn-on time	t _{on}	I _C = -1 A, I _{B1} = -0.1 A, I _{B2} = 0.1 A	0.5			μs
Storage time	t _{stg}		1.2			μs
Fall time	t _f		0.3			μs

■ hFE Classification

Rank	Q	P
h _{FE}	70~150	120~250